

**Unchanged Claim 11:**

11. The process of claim 8, wherein the ejecting includes directing light from a pulsed laser onto the body.

**Unchanged Claim 12:**

12. The process of claim 8, wherein the substrate comprises one of SiC, LaAlO<sub>3</sub>, SiO<sub>2</sub>, SrTiO<sub>3</sub>, and sapphire.

**Unchanged Claim 13:**

13. The process of claim 8, wherein the ejecting and growing are performed in a vacuum chamber that is maintained at a pressure of less than about 10<sup>-2</sup> Torr.

**Unchanged Claim 14:**

14. The process of claim 14, wherein the ejecting and growing are performed in a vacuum chamber that is maintained at a pressure of greater than about 10<sup>-6</sup> Torr.

**Unchanged Claim 15:**

15. The process of claim 13, wherein the growing produces a crystalline or polycrystalline layer of MgB<sub>2</sub> whose thickness is at least 10 nm.

**REMARKS**

Pending Claims

Independent claim 8 and dependent claims 9-15 are pending.

Amendments

Claim 8 has been amended to explicitly recite that the growing step produces a MgB<sub>2</sub> layer.

Applicants respectfully request admission of the amendment under 37 CFR 1.116 (c), because good and sufficient reasons exist why the amendment is necessary and was not earlier presented as discussed below. First, Applicants previously believed that the